



SUTS324□□-G Series
SUTW324□□-G Series EMI/EMS Test results

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No.	Test item	Conditions	Conditions of Acceptability	Result
1	Line conduction	(1) Rated input (2) Rated load (3) Ambient temp. 25±10°C (4) Testing circuitry Fig.1	(1)Meets the undermentioned FCC Part15 classA , VCCI classA CISPR22 classA , EN55022-A	O.K.
2	Radiated emission	(1) Rated input (2) Rated load (3) Ambient temp. 25±10°C (4) Testing circuitry Fig.1	(1)Meets the undermentioned FCC Part15 classA , VCCI classA CISPR22 classA , EN55022-A	O.K.
3	Static electricity immunity test (EN61000-4-2)	(1) Rated input (2) Rated load (3) Ambient temp. 25±10°C (4) Contact discharge voltage 8[kV] (EN61000-4-2 Level 4) (5) Testing circuitry Fig.1	(1)No protection circuit failure. (2)No output voltage drop with control circuit failure. (3)No any other function failure	O.K.
4	Radiated, radio-frequency, electromagnetic field immunity test (EN61000-4-3)	(1) Rated input (2) Rated load (3) Ambient temp. 25±10°C (4)Testing field strength 10[V/m] (EN61000-4-3 Level 3) (5) Testing circuitry Fig.1	(1)No protection circuit failure. (2)No output voltage drop with control circuit failure. (3)No any other function failure	O.K.
5	Electrical fast transient/ burst immunity test (EN61000-4-4)	(1) Rated input (2) Rated load (3) Ambient temp. 25±10°C (4) Test peak voltage 4[kV] (IEC61000-4-4 Level 4) (5) Testing circuitry Fig.1	(1)No protection circuit failure. (2)No output voltage drop with control circuit failure. (3)No any other function failure	O.K.
6	Surge immunity test (EN61000-4-5)	(1) Rated input (2) Rated load (3) Ambient temp. 25±10°C (4) Test voltage Line to line 2[kV] (Level 3) (5) Testing circuitry Fig.2	(1)The power supply is not stc (2)Circuit does not malfunction. (3)No abnormality of the insulation destruction etc. (4)Parts are no damaged.	O.K.



○ Testing circuitry

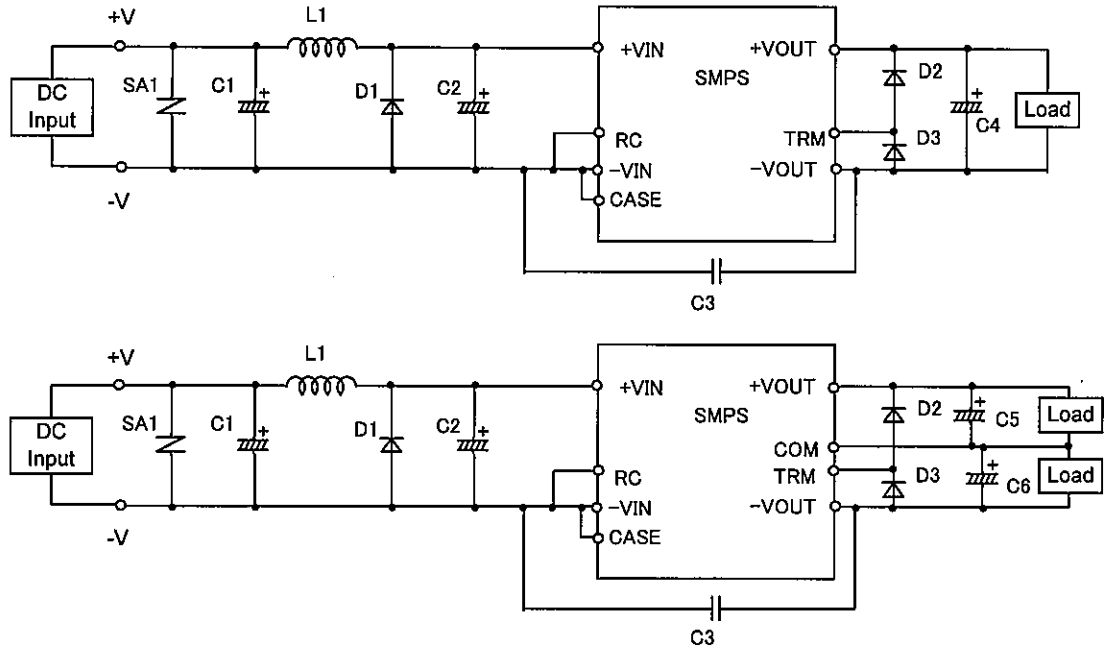


Fig.1 Testing circuitry

C1	:	50V	100 μ F	UPW1H101M	(NICHICON)
C2	:	50V	47 μ F	UPW1H470M	(NICHICON)
SA1	:	47V	ERZV10D470	(MATSUSHITA ELECTRONICS)	
L1	:	10 μ H	CY3H-100	(KORINELECTRONICS)	
D1	:	3A	200V	ERD32-02	(FUJI ELECTRIC)
D2,D3	:	1A	100V	S5566B	(TOSHIBA)
C3	:	2000V	100pF	CF42W5R101K2000A	(KYOCERA)
C4	:	SUTS3243R3-G	25V	220 μ F	UPW1E221M (NICHICON)
		SUTS32405-G	25V	220 μ F	UPW1E221M (NICHICON)
		SUTS32412-G	25V	100 μ F	UPW1E101M (NICHICON)
		SUTS32415-G	25V	100 μ F	UPW1E101M (NICHICON)
C5,6	:	SUTW32412-G	25V	100 μ F	UPW1E101M (NICHICON)
		SUTW32415-G	25V	100 μ F	UPW1E101M (NICHICON)

○ Testing circuitry

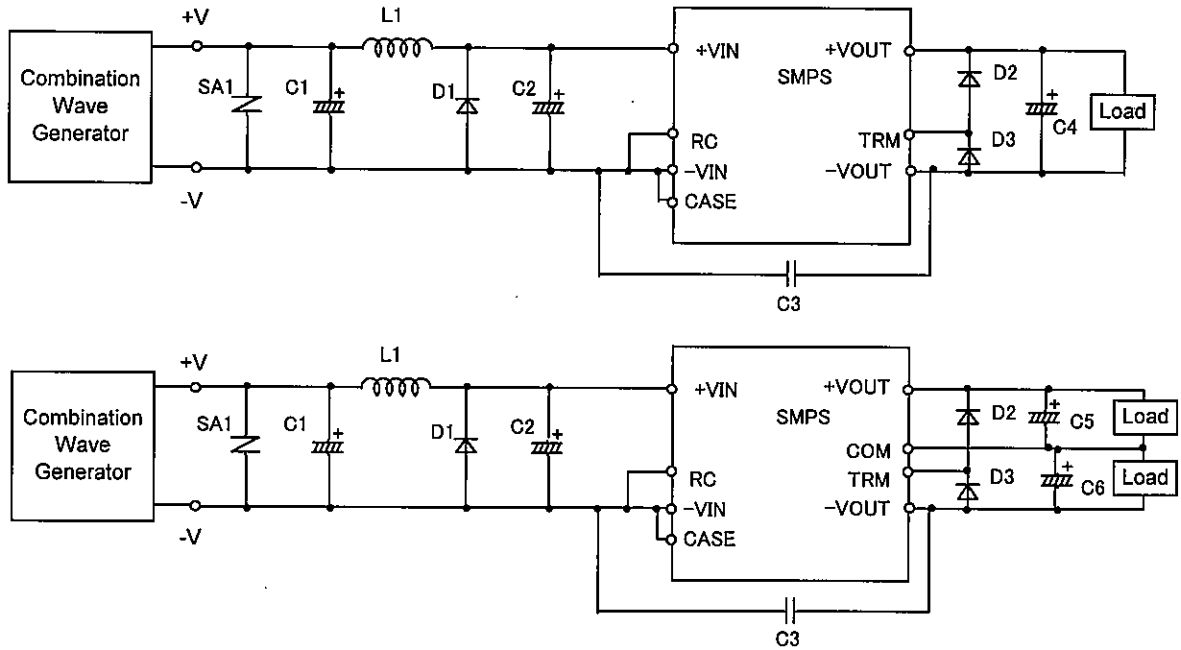


Fig.2 Testing circuitry

C1	:	50V	100 μ F	UPW1H101M	(NICHICON)
C2	:	50V	47 μ F	UPW1H470M	(NICHICON)
SA1	:	47V	ERZV10D470	(MATSUSHITA ELECTRONICS)	
L1	:	10 μ H	CY3H-100	(KORINELECTRONICS)	
D1	:	3A	200V	ERD32-02	(FUJI ELECTRIC)
D2,D3	:	1A	100V	S5566B	(TOSHIBA)
C3	:	2000V	100pF	CF42W5R101K2000A	(KYOCERA)
C4	:	SUTS3243R3-G	25V	220 μ F	UPW1E221M (NICHICON)
	:	SUTS32405-G	25V	220 μ F	UPW1E221M (NICHICON)
	:	SUTS32412-G	25V	100 μ F	UPW1E101M (NICHICON)
	:	SUTS32415-G	25V	100 μ F	UPW1E101M (NICHICON)
C5,6	:	SUTW32412-G	25V	100 μ F	UPW1E101M (NICHICON)
	:	SUTW32415-G	25V	100 μ F	UPW1E101M (NICHICON)